



60V DUAL NPN LOW SAT TRANSISTOR IN DFN2020-6

Features

- BV_{CEO} > 60V
- I_C = 1A High Continuous Collector Current
- R_{CE(sat)} = 180mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(sat)} < 220mV @ 1A
- P_D up to 2.47W for Power-Demanding Applications
- R_{θJA} Efficient, 40% Lower than SOT26
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DSS4160FDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

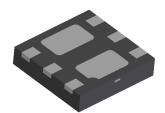
Mechanical Data

- Package: U-DFN2020-6 (Type B)
- Package Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

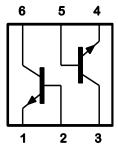
Application

- Load switches
- Power management
- · Charging circuits
- Power switches (e.g. motors, fans)

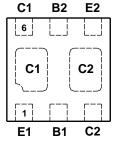
U-DFN2020-6 (Type B)



Bottom View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

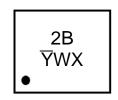
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS4160FDBQ-7	Automotive	2B	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

U-DFN2020-6 (Type B)



2B = Product type Marking Code $\overline{Y} = Year: 0~9$

W = Week: $A \sim Z = 1 \sim 26$ Week; $A \sim Z = 27 \sim 52$ Week;

Z Represents 52 and 53 Week X = A~Z: Internal Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Collector Current	I _{CM}	1.5	Α
Base Current	Ι _Β	300	mA
Peak Base Current	I _{BM}	1	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5, 7)		405		
Power Dissipation	(Note 5, 8)	Б	510	mW	
Prower Dissipation	(Note 6, 7)	P _D	1650		
	(Note 6, 8)		2470		
	(Note 5, 7)		308		
Thermal Resistance, Junction to Ambient	(Note 5, 8)		245	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6, 7)	$R_{\theta JA}$	76	C/VV	
	(Note 6, 8)		51	I	
Thermal Resistance, Junction to Lead	(Note 9)	$R_{ heta JL}$	18	°C/W	
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 10)

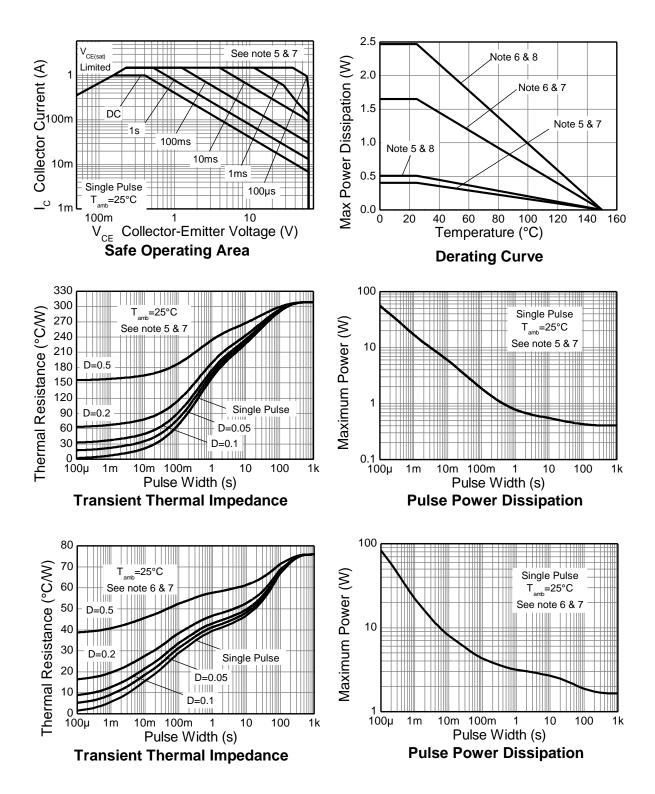
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3

Notes:

- 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6 Same as Note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
- 7. For a dual device with one active die.
- 8. For dual device with two active die running at equal power.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pads).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





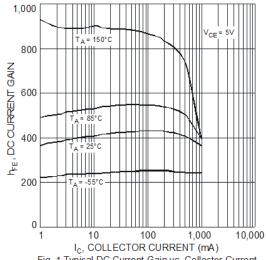
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

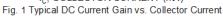
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	60	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	$I_E = 100\mu A$
Collector-Base Cutoff Current		_	_	100	nA	$V_{CB} = 48V, I_{E} = 0$
Collector-base outon current	I _{CBO}	_		50	μA	$V_{CB} = 48V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_		100	nA	$V_{EB} = 5.6V, I_C = 0$
		290	430		_	$V_{CE} = 2V, I_{C} = 100mA$
DC Current Gain (Note 11)	h _{FE}	150	220			$V_{CE} = 2V, I_{C} = 500mA$
		70	110			$V_{CE} = 2V$, $I_C = 1A$
		_	90	120		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	170	220	mV	$I_C = 1A$, $I_B = 100mA$
		_	185	240		$I_C = 1A$, $I_B = 50mA$
Equivalent On-Resistance (Note 11)	R _{CE(sat)}	_	180	240	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	_	1	V	$I_C = 0.5A$, $I_B = 50mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	1.1		$I_C = 1A$, $I_B = 50mA$
		_	_	1.1		$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}	_	_	0.9	V	$V_{CE} = 2V, I_{C} = 0.5A$
Transition Frequency	f⊤	90	175	_	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Output (Collector) Capacitance	C _{obc}	_	4	6	pF	$V_{CB} = 10V$, $f = 1MHz$
Turn-On Time	t _{on}	_	105	_	ns	
Delay Time	t _d	_	15	_	ns	
Rise Time	t _r	_	90	_	ns	$V_{CC} = 10V, I_{C} = 0.5A,$
Turn-Off Time	t _{off}	_	540	_	ns	$I_{B1} = -I_{B2} = 25\text{mA}$
Storage Time	ts	_	410	_	ns	
Fall Time	t _f	_	130		ns	

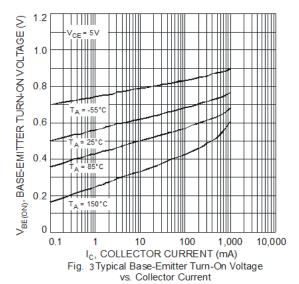
Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

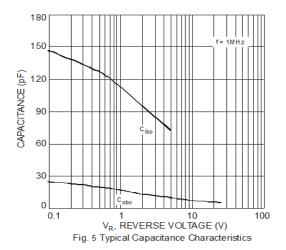


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









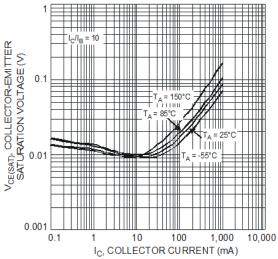
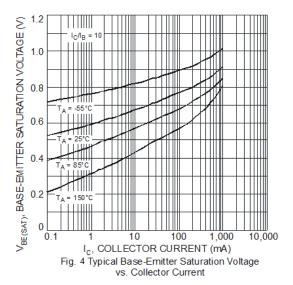


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current



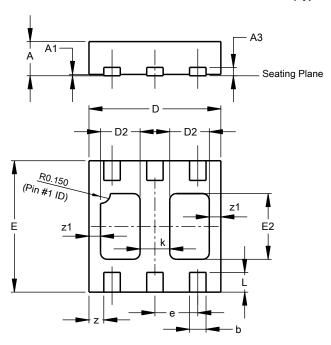
DSS4160FDBQ 5 of 7 www.diodes.com Datasheet Number: DS44647 Rev. 1 - 2



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

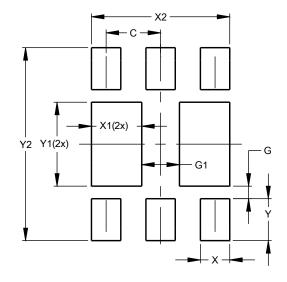


U-DFN2020-6 Type B					
Dim	Min	Max	Тур		
Α	0.545	0.605	0.575		
A1	0.00	0.05	0.02		
A3	_	_	0.13		
b	0.20	0.30	0.25		
D	1.95	2.075	2.00		
D2	0.50	0.70	0.60		
е	-	_	0.65		
Е	1.95	2.075	2.00		
E2	0.90	1.10	1.00		
k	-	_	0.45		
L	0.25	0.35	0.30		
Z	_	_	0.225		
z1	_	_	0.175		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)		
C	0.650		
G	0.150		
G1	0.450		
Х	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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